PROCESS CP734V

Small Signal Transistors

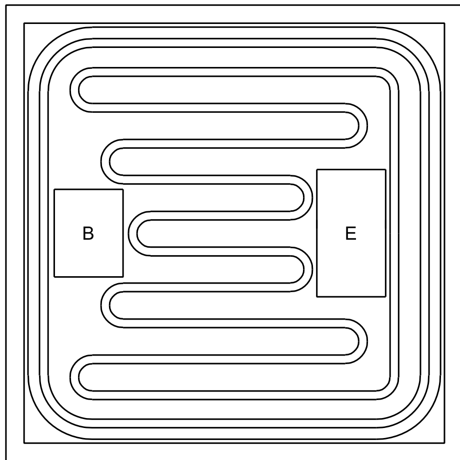
PNP - Chopper Transistor Chip

www.DataSheet4U.com

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	31.5 x 31.5 MILS
Die Thickness	7.0 MILS
Base Bonding Pad Area	4.7 x 6.7 MILS
Emitter Bonding Pad Area	4.7 x 8.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 5 INCH WAFER
16,986

PRINCIPAL DEVICE TYPES
CMPT404A
MPS404A

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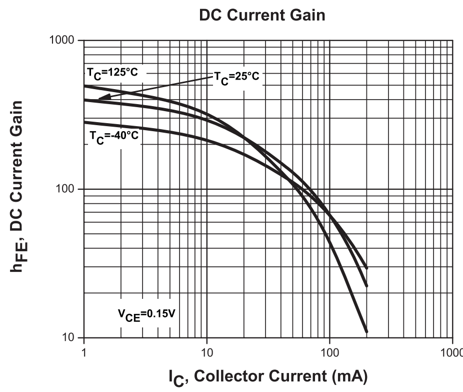
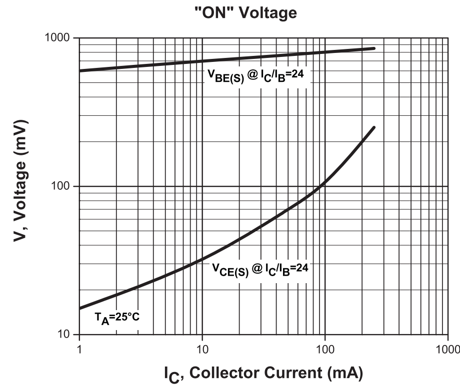
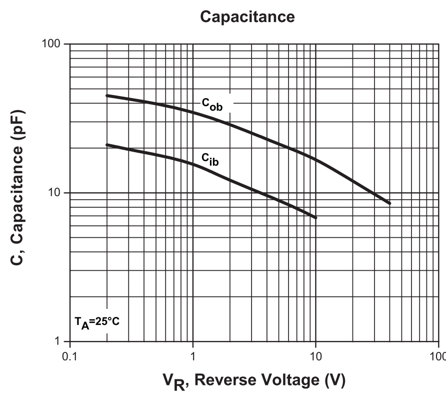
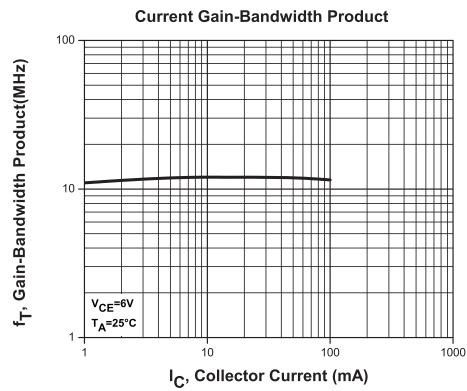
PROCESS CP734V

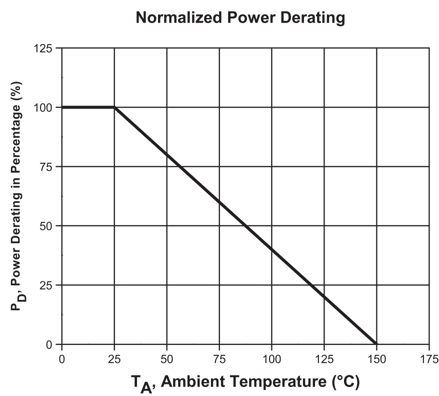
Typical Electrical Characteristics











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